

Vishay Siliconix

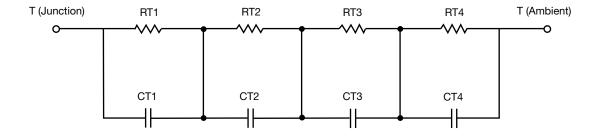
# **R-C Thermal Model Parameters**

### **DESCRIPTION**

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

#### **R-C THERMAL MODEL FOR TANK CONFIGURATION**



R-C VALUES FOR TANK	IES FOR TANK CONFIGURATION				
	THERMAL RES	ISTANCE (°C/W)			
Junction to	Ambient	Case	Foot		
RT1	11.9104	156.7492m	N/A		
RT2	3.1921	140.2608m	N/A		
RT3	931.0189m	215.9481m	N/A		
RT4	23.9695	135.1361m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	8.2562	3.0729m	N/A		
CT2	1.0641	21.0087m	N/A		
CT3	147.3202m	92.2141m	N/A		
CT4	4.0108	250.0254m	N/A		

#### Note

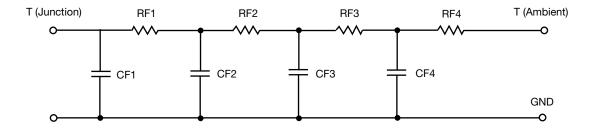
• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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## **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RF1	884.7234m	234.4011m	N/A		
RF2	6.5762	229.4657m	N/A		
RF3	23.1425	146.6653m	N/A		
RF4	9.4830	38.4063m	N/A		
	THERMAL CAPAC	TANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	24.3391m	2.7088m	N/A		
CF2	882.6174m	26.1012m	N/A		
CF3	1.7594	105.9528m	N/A		
CF4	2.6137	170.9393m	N/A		

### Note

• n/a indicates not applicable





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